



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

KTA1668 TRANSISTOR(PNP)

FEATURES

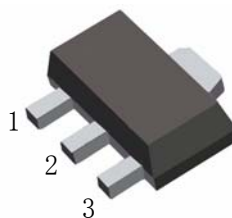
- High voltage: $V_{CEO}=-60V$
- High transistors frequency

MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-1	A
P_C	Collector power dissipation	500	mW
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

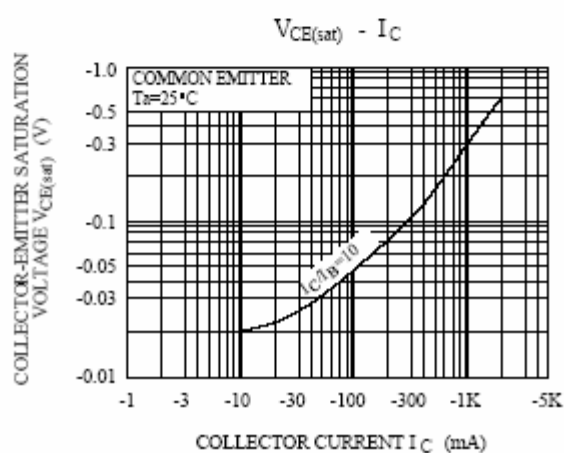
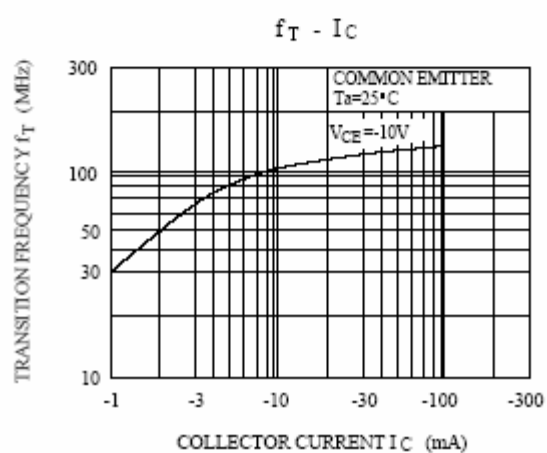
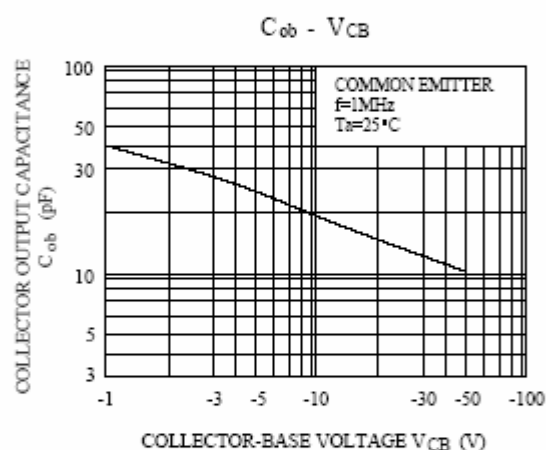
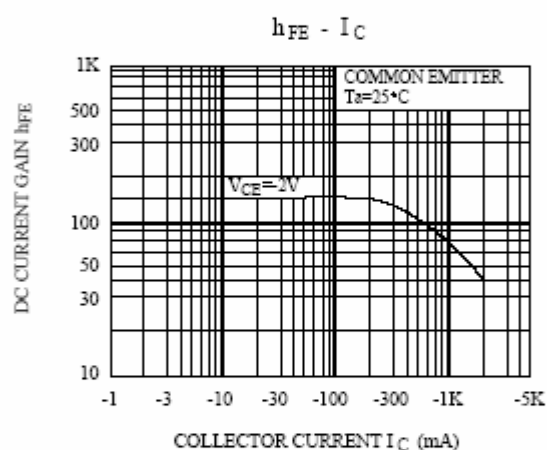
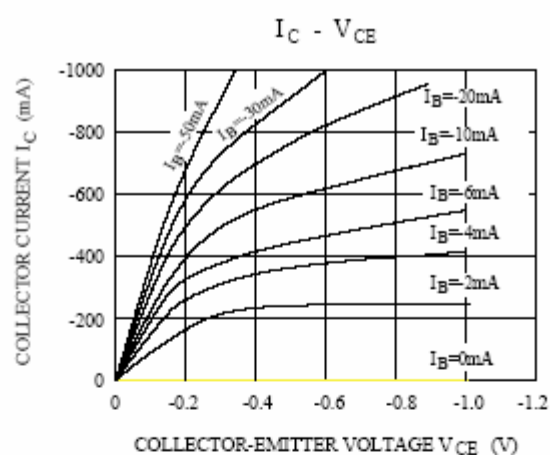
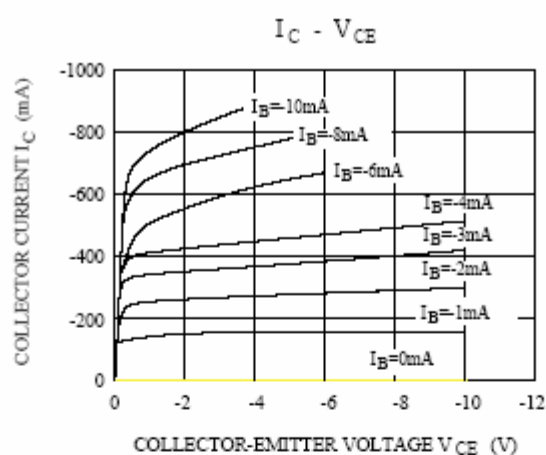
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1mA, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1mA, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.1	μA
DC current gain	h_{FE1}	$V_{CE}=-2V, I_C=-50mA$	60		200	
	h_{FE2}	$V_{CE}=-2V, I_C=-1A$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$			-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500mA, I_B=-50mA$			-1.2	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA, f=100MHz$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		12		pF

CLASSIFICATION OF h_{FE}

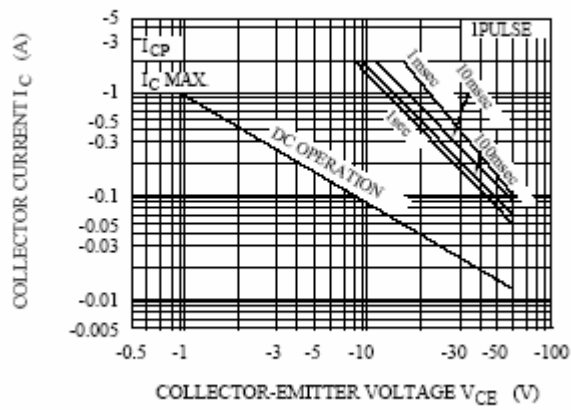
Rank	O	Y
Range	60-120	100-200
Marking	JO	JY

Typical Characteristics

KTA1668



SAFE OPERATING AREA

 $P_C - T_a$ 